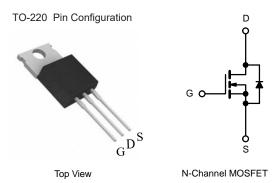


DTP110N12 www.din-tek.jp

N-Channel 120 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	R _{DS(on)} (Ω) MAX.	I _D (A)	Q _g (TYP.)			
120	0.0075 at V_{GS} = 10 V	110	63 nC			



FEATURES

- DT-TrenchPower MOSFET
- Maximum 175 °C junction temperature
- 100 % R_g and UIS tested

APPLICATIONS

- Power supplies:
 - Uninterruptible power supplies
 - AC/DC switch-mode power supplies
 - Lighting
- Synchronous rectification
- DC/DC converter
- Motor drive switch
- DC/AC inverter
- Solar micro inverter
- Class D audio amplifier
- Battery management

ABSOLUTE MAXIMUM RATINGS ($T_c = 25 \text{ °C}$, unless otherwise noted)							
PARAMETER	SYMBOL	LIMIT	UNIT				
Drain-Source Voltage	V _{DS}	120					
Gate-Source Voltage	V _{GS}	± 20	- V				
	T _C = 25 °C	1-	110				
Continuous Drain Current ($T_J = 150 \ ^{\circ}C$)	T _C = 125 °C	I _D	75	_			
Pulsed Drain Current (t = 100 µs)	I _{DM}	440	— A				
Avalanche Current	L = 0.1 mH		100				
Single Avalanche Energy ^a	L = 0.1 MH	E _{AS}	205	mJ			
Maximum Dower Dissipation #	T _C = 25 °C	р	385 ^b	w			
Maximum Power Dissipation ^a	T _C = 125 °C	– P _D –	156 ^b	v			
Operating Junction and Storage Temperature F	T _J , T _{stg}	-55 to +175	°C				

THERMAL RESISTANCE RATINGS						
PARAMETER	SYMBOL	LIMIT	UNIT			
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	40	°C/W			
Junction-to-Case (Drain)	R _{thJC}	0.4	0/10			

Notes

- a. Duty cycle \leq 1 %.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).



SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V _{DS}	V_{GS} = 0 V, I_D = 250 μ A	120	-	-	V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},\ I_D=250\ \mu A$	2	-	5	v	
Gate-Body Leakage	I _{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V	-	-	± 100	nA	
		$V_{DS} = 120 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} = 120 V, V_{GS} = 0 V, T_{J} = 125 $^{\circ}C$	-	-	100	μA	
		V_{DS} = 120 V, V_{GS} = 0 V, T_{J} = 175 °C	-	-	2	mA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \geq 10 \ V, \ V_{GS} = 10 \ V$	110	-	-	А	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}$	-	0.0075	0.0090	Ω	
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 10 \text{ A}$	-	52	-	S	
Dynamic ^b							
Input Capacitance	C _{iss}		-	5607	-	pF	
Output Capacitance	C _{oss}	V_{GS} = 0 V, V_{DS} = 75 V, f = 1 MHz	-	1235	-		
Reverse Transfer Capacitance	C _{rss}		-	76	-		
Total Gate Charge ^c	Qg		-	63	95	nC	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 75 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$	-	18	-		
Gate-Drain Charge ^c	Q _{gd}		-	25	-		
Gate Resistance	R _g	f = 1 MHz	1.5	3	5	Ω	
Turn-On Delay Time ^c	t _{d(on)}		-	15	-		
Rise Time ^c	t _r	V_{DD} = 75 V, R_L = 1.25 Ω	-	114	-	20	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 30$ A, V_{GEN} = 10 V, R_g = 1 Ω	-	28	-	ns	
Fall Time ^c	t _f		-	8	-	1	
Drain-Source Body Diode Ratings and	nd Characteri	stics ^b (T _C = 25 °C)					
Pulsed Current (t = 100 μs)	I _{SM}		-	-	440	А	
Forward Voltage ^a	V _{SD}	$I_F = 10 \text{ A}, V_{GS} = 0 \text{ V}$	-	0.75	1.2	V	
Reverse Recovery Time	t _{rr}		-	105		ns	
Peak Reverse Recovery Charge	I _{RM(REC)}	I _F = 10 A, di/dt = 100 A/μs	-	10		А	
Reverse Recovery Charge	Q _{rr}		-	0.5		μC	

Notes

a. Pulse test; pulse width $\leq 300~\mu\text{s},$ duty cycle $\leq 2~\%.$

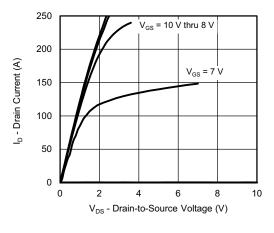
b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

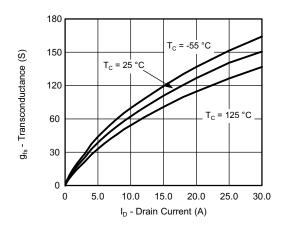
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



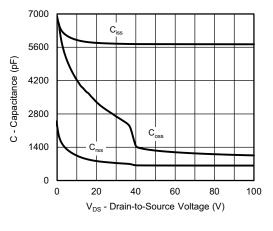
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



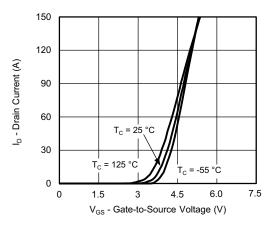
Output Characteristics



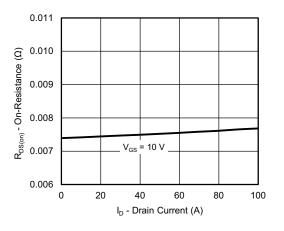
Transconductance



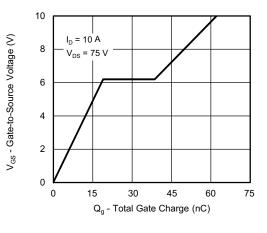
Capacitance



Transfer Characteristics



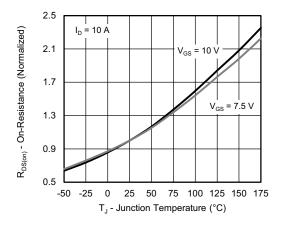
On-Resistance vs. Drain Current



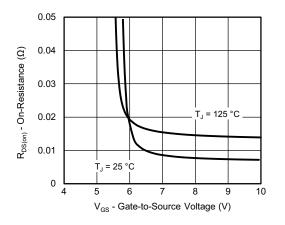
Gate Charge



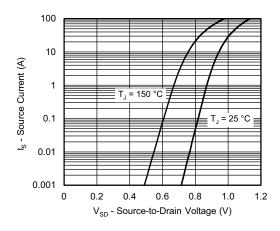
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



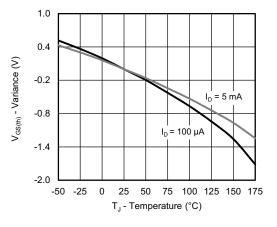
On-Resistance vs. Junction Temperature



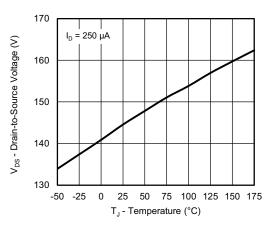
On-Resistance vs. Gate-to-Source Voltage



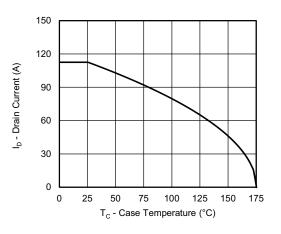
Source Drain Diode Forward Voltage



Threshold Voltage

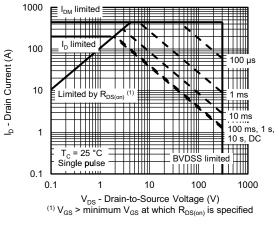


Drain Source Breakdown vs. Junction Temperature

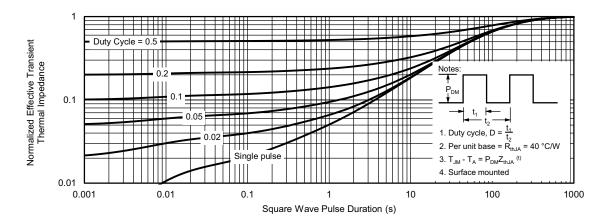


Current De-Rating

THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



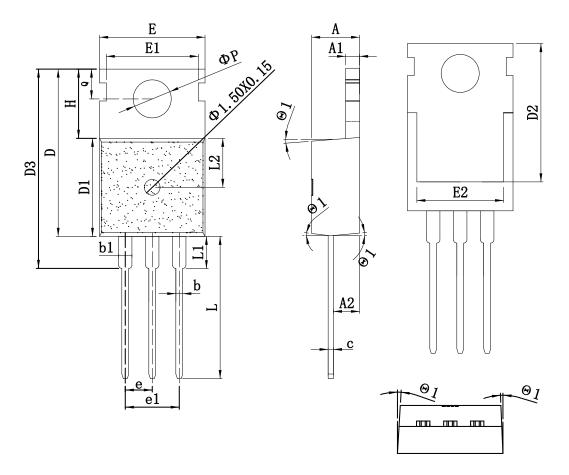
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



TO-220_3L-A PACKAGE OUTLINE

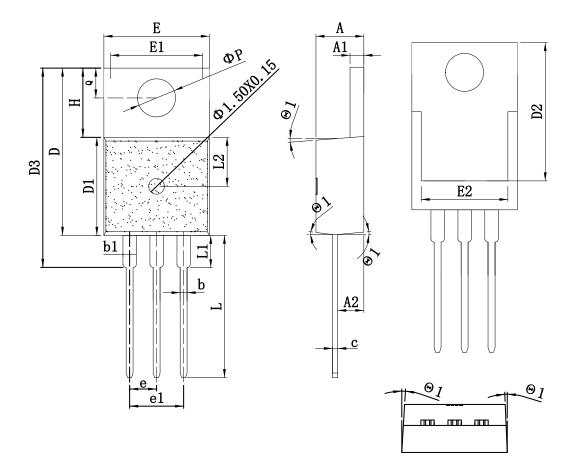


COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMPOL	SYMBOL mm			SYMBOL	mm		
SIMBOL	MIN	TYP	MAX	SIMBOL	MIN	TYP	MAX
А	4.15	4.50	4.80	E1	8.25	8.70	9.15
A1	1.15	1.30	1.50	E2	7.20	8.00	8.80
A2	2.10	2.40	2.65	e	2.38	2.54	2.74
b	0.65	0.80	1.00	e1	5.08REF		
b1	1.10	1.33	1.80	Н	6.20	6.50	6.90
с	0.35	0.50	0.65	L	12.75	13.28	13.70
D	14.25	15.75	16.15	L1	-	-	3.50
D1	8.70	9.20	9.60	L2	2.30	4.65	7.00
D2	12.30	13.10	13.85	φP	3.40	3.65	3.85
D3	16.20	18.80	20.60	Q	2.50	2.80	3.00
Е	8.68	10.02	11.00	θ	2°	-	7°



TO-220_3L-B PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	mm			SYMBOL	mm		
SIMBOL	MIN	TYP	MAX	SIMBOL	MIN	TYP	MAX
А	4.15	4.50	4.80	E1	8.25	8.70	9.15
A1	1.15	1.30	1.50	E2	7.20	8.00	8.80
A2	2.10	2.40	2.65	е	2.38	2.54	2.74
b	0.65	0.80	1.00	e1	5.08REF		
b1	1.10	1.33	1.80	Н	6.20	6.50	6.90
с	0.35	0.50	0.65	L	12.75	13.28	13.70
D	14.25	15.75	16.15	L1	-	-	3.50
D1	8.70	9.20	9.60	L2	2.30	4.65	7.00
D2	12.30	13.10	13.85	φP	3.40	3.65	3.85
D3	16.20	18.80	20.60	Q	2.50	2.80	3.00
Е	8.68	10.02	11.00	θ	2°	-	7°



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